# ne<mark>x</mark>peria

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Kind regards,

Team Nexperia

**PNP/PNP resistor-equipped transistors;** R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 

Rev. 03 — 1 September 2009

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

PNP/PNP resistor-equipped transistors

Table 1.	Product	overview
		0.0.0.0.0

Type number	Package		NPN/PNP	NPN/NPN
	NXP	JEITA	complement	complement
PEMB17	SOT666	-	PEMD17	PEMH17
PUMB17	SOT363	SC-88	PUMD17	PUMH17

#### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

#### **1.3 Applications**

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

#### 1.4 Quick reference data

#### Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
lo	output current (DC)		-	-	-100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.37	0.47	0.57	



1

| | 2 3 *006aaa212* 

**PNP/PNP** resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 

# 2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

# 3. Ordering information

ring inform	ation	
Package		
Name	Description	Version
-	plastic surface mounted package; 6 leads	SOT666
SC-88	plastic surface mounted package; 6 leads	SOT363
	Package Name -	Name         Description           -         plastic surface mounted package; 6 leads

### 4. Marking

Marking code <sup>[1]</sup>
5M
B*8

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong \* = t: made in Malaysia

\* = W: made in China

#### PNP/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$

## 5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-40	V
lo	output current (DC)		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	200	mW
	SOT666		<u>[1] [2]</u> _	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, standard footprint.

[2] Reflow soldering is the only recommended soldering method.

## 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1] [2] _	-	625	K/W
Per device	9					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		<u>[1] [2]</u>	-	416	K/W

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMB17\_PUMB17\_3
Product data sheet

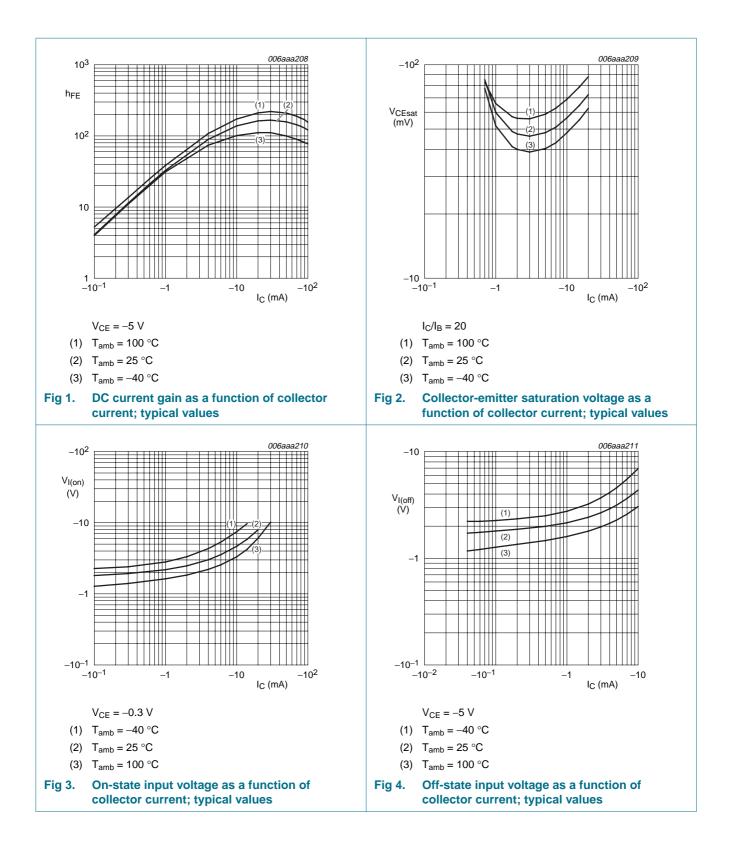
# 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	-1	μA
	cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A};$ T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-110	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5$ V; $I_C = -5$ mA	60	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA}; I_{B} = -0.5 \text{ mA}$	-	-	-150	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -100 \mu\text{A}$	-	-1.7	-1.2	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -2 \text{ mA}$	-4	-2.7	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.37	0.47	0.57	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF

#### **NXP Semiconductors**

# PEMB17; PUMB17

PNP/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 



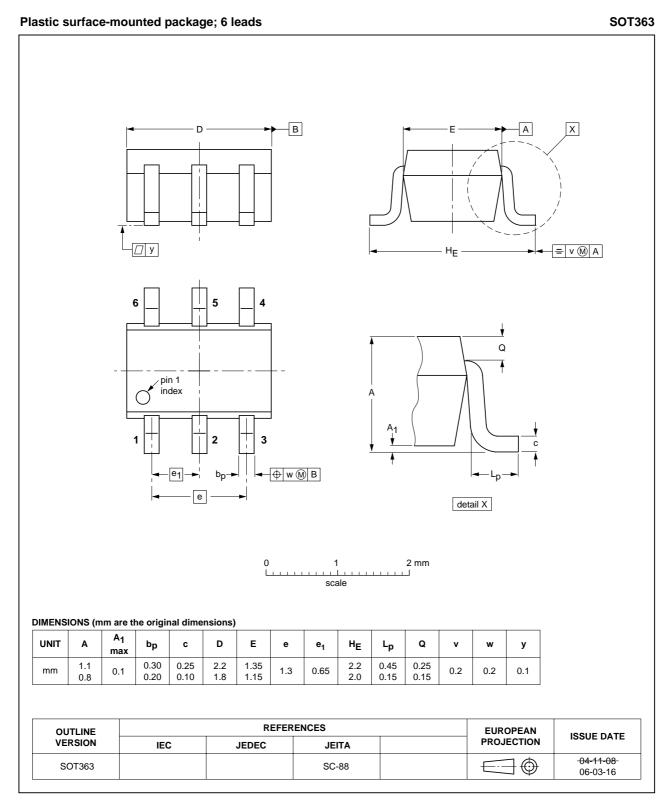
PEMB17\_PUMB17\_3
Product data sheet

#### **NXP Semiconductors**

PEMB17; PUMB17

PNP/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 

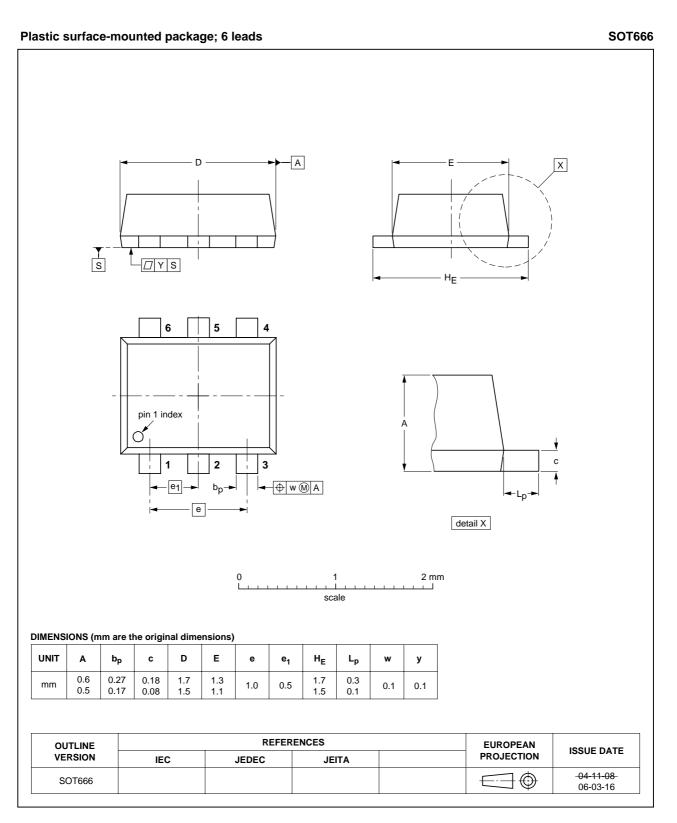
## 8. Package outline



#### Fig 5. Package outline SOT363 (SC-88)

PEMB17\_PUMB17\_3
Product data sheet

PNP/PNP resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 



#### Fig 6. Package outline SOT666

PEMB17\_PUMB17\_3 Product data sheet

# 9. Packing information

#### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing o	juantity	
			3000	4000	10000
PEMB17	SOT666	4 mm pitch, 8 mm tape and reel;	-	-115	-
PUMB17	SOT363	4 mm pitch, 8 mm tape and reel; T1	2 -115	-	-135
PUMB17	SOT363	4 mm pitch, 8 mm tape and reel; T2	<u>3</u> -125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

# **10. Revision history**

Table 10. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB17_PUMB17_3	20090901	Product data sheet	-	PEMB17_PUMB17_2
Modifications:	including nev content.	eet was changed to reflect w legal definitions and disc	aimers. No changes w	
		ckage outline SOT363 (SC		
	<ul> <li>Figure 6 "Pa</li> </ul>	ckage outline SOT666": up	dated	
PEMB17_PUMB17_2	20050203	Product data sheet	-	PUMB17_1
PUMB17_1	20031103	Product specification	-	-

# **11. Legal information**

#### 11.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PEMB17\_PUMB17\_3
Product data sheet

#### **NXP Semiconductors**

# PEMB17; PUMB17

**PNP/PNP** resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 22 k $\Omega$ 

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